

Thermal Design Considerations

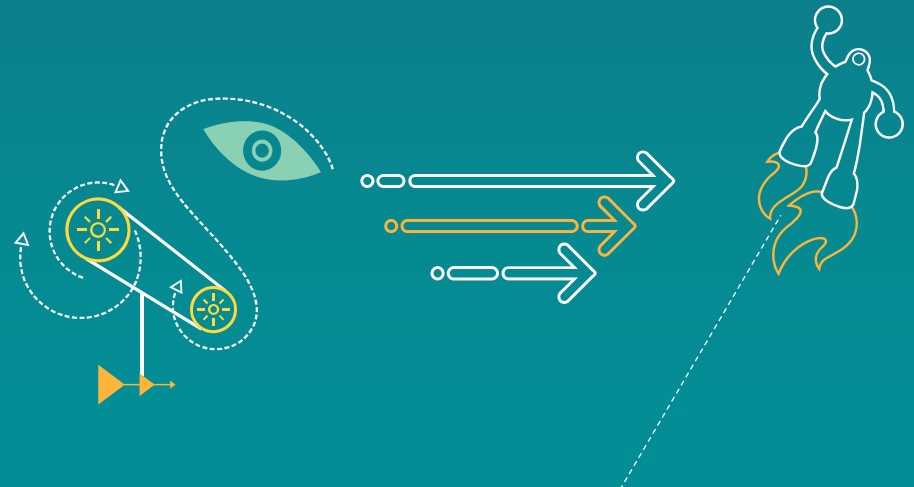


Qualcomm Technologies, Inc.

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Revision History

Revision	Date	Description
A	November 2009	Initial release
B	March 2010	Page 5 – Added additional information on chipset power contribution Page 6 – Updated the carrier requirements description Page 8 – Updated the QCT MDM8200™ prototype dongle information Page 9 – Updated Plastic or mechanical selection information Deleted former page 10 – Simple Heat Dissipation Modeling Page 11 – Added additional information on the assumptions made by the Simple Heat Dissipation model Page 14 – Updated temperature value to 140 in third Conclusions bullet Added PA temperature in last Other bullet Updated text in fourth Other bullet Page 15 – Updated steady state PA temperature Page 16 – Updated values in Results bullet, step 1 and step 2
C	June 2010	Updated title to Thermal Design Consideration Application Note Page 5 – Added smart phone form factor as area of focus Page 9 – Updated bullet text under number 4 Pages 10 and 11 – New slides with additional thermal design considerations
D	November 2010	Pages 9, 10, 11 – Added additional thermal design approaches Pages 12, 13 – Added routing examples Pages 27, 28, 29 – Added information on thermal tests and their results Pages 5, 30 – Updated references
E	December 2013	Removed <i>Experiment: Solid Copper vs. Paste Vias</i> slide Added new slide 29, <i>Miscellaneous Thermal Experiments - Qualcomm FFA</i> Added new slide 30, <i>Factors That Enhance Thermal for PCB</i> Added new slide 31, <i>PCB Topology and Fabrication Technology Impact on Thermal</i> Updated title for slide 32, <i>PCB Components Placement Thermal Design Guidance</i>

Agenda

■ Introduction

■ Thermal design approach, simulation, and testing:

- Thermal design guidelines, approach, and trade-offs
 - ◆ Applying thermal fundamentals during the conceptual stage of a product design
 - ◆ Used to drive trade-offs for cooling method, size, part location, etc.
- Thermal simulation
- Simple heat dissipation modeling
 - ◆ 3D computational fluid dynamics software used to predict flow and temperature
- Thermal testing
 - ◆ Measured temperature used to validate design intent and may drive redesign

■ Appendix: Heat transfer fundamentals:

- Thermal resistance equation
- Heat transfer modes
 - ◆ Conduction
 - ◆ Convection
 - ◆ Radiation
- Qualcomm® MDM8200-based prototype USB dongle resistances example



Introduction

Introduction

- Purpose:
 - The purpose of this application note is to assist OEMs with the proper thermal design of:
 - USB dongle form factors
 - Smart phone form factors heat dissipation
- Background:
 - Due to the small form factor of USB dongles, there is less surface area to dissipate heat.
 - Even though smart phones have a bigger form factor, heat dissipation is still a problem.
 - Heat generated by the device can greatly impact the end user experience and introduce health and safety concerns.
 - High MDM8k/9k power consumption (> 1 W) is due to the new architecture for increased data throughput.
 - PA power (> 1 W), along with the MDM/MSM™, are the highest power contributors.
- References:
 - *Thermal Protection Algorithm Overview* (80-VT344-1)
 - *MDM8200 Thermal Protection Algorithm Application Note* (80-VJ372-14)

Note: The thermal protection algorithm is a software thermal mitigation algorithm that can help improve thermal performance of existing hardware designs.

International Standards and Carrier Requirements

- Several governing standards:
 - US: Underwriters Lab 60950 specification from Part 2 of Table 4A (Section 4.5.1, temperature rises). The applicable part in that table as understood should be "Handles, knobs, grips, etc., continuously held in normal use." The maximum temperature in the UL specification is 75°C (167°F) for plastic.
 - EU: 1991 copy of the IEC specification: 610.1 (more medical) Clause 42, has a "continuously held" molded plastic device at a maximum temperature of 75°C.
 - Asia: TBD
- Carrier requirements:
 - Carriers are starting to define strict thermal specifications.
 - i.e., AT&T stated devices and associated accessories being submitted for technical acceptance shall not exceed the touch temperature limits defined by the most current version of UL 60950-1.



Thermal Design – Approach, Simulation, and Testing

Thermal Design Approach

- Thermal design guidelines:
 - Apply thermal fundamentals during the conceptual stage of a product design.
 - Drive trade-offs for cooling method, size, part location, etc.
- 1. Increase surface area of the printed wiring board (PWB) and housing with consideration of industrial design goals.
- 2. Gather power dissipation and size of each heat generating item or component. Prioritize cooling based on power density, watts per inch squared W/in^2 .
 - QCT MDM8200 prototype dongle example: Cell PA is 76 W/in^2 ($1.07 \text{ W}/1/8'' \text{ sq.}$), and MDM is 3.5 W/in^2 ($1.2 \text{ W}/15 \text{ mm sq.}$).
- 3. Gather the maximum junction or surface temperature rating of parts and prioritize by temperature; ambient ratings of parts should not be used.

Thermal Design Approach (cont.)

4. Material selection, color, and finish: Aluminum is 1000 times more conductive than plastic. White and painted surfaces have higher emissivity (high e – low R – low ΔT) than black or rough surfaces.
 - Metals conduct heat better than plastic. Metals have a lower touch temperature rating because they can conduct heat to fingers faster than plastics. When metals are used instead of plastic for electronics packaging, they can reduce peak heat source temperatures, but the packaging can reach a higher temperature.
5. Avoid co-locating high-power density parts side-by-side or front-to-back on the single PWB or face to face on two parallel PWBs.
 - Keep PA away from other heat sources
 - Keep very hot components away from a battery.
 - Keep the PMIC away from the MDM device.
 - Keep VCTCXO or any XO away from heat sources/gradients.
6. Plastic or mechanical selection:
 - Use proper heat vents that allow heat escape.
 - Thermal resistance is proportional to wall thickness.
 - Use ribbing for extra surface area for a given form factor.

Thermal Design Approach (cont.)

7. Provide a low-resistance cooling path for small and other critical components.

- Mount components on the top side of the PWB for better natural convection.
- Increase the conductivity of the PWB with added layers and copper on each layer.
- A higher copper density provides better thermal relief/heat transport.
 - The power amplifier is too small to rely on air dissipation only. A large amount of copper in the PWB is necessary to help heat sink the thermal load.
 - Fill empty board layers with copper wherever possible.
 - Layer 1 copper is very important
 - Increase copper using thick traces as much as possible . Especially recommended for voltage rails that consume high current.
- Add ample PWB vias under or near hot spots.
 - Vias should go to a large radiating plane for better heat dissipation.
 - Via material is important . Solid copper has higher thermal conductivity than paste.
 - Stacked vias are better than staggered
 - Vias in PA ground pad are very important. Put as many as you can. Stacked vias to the ground pad is best
- Use power planes instead of routing.

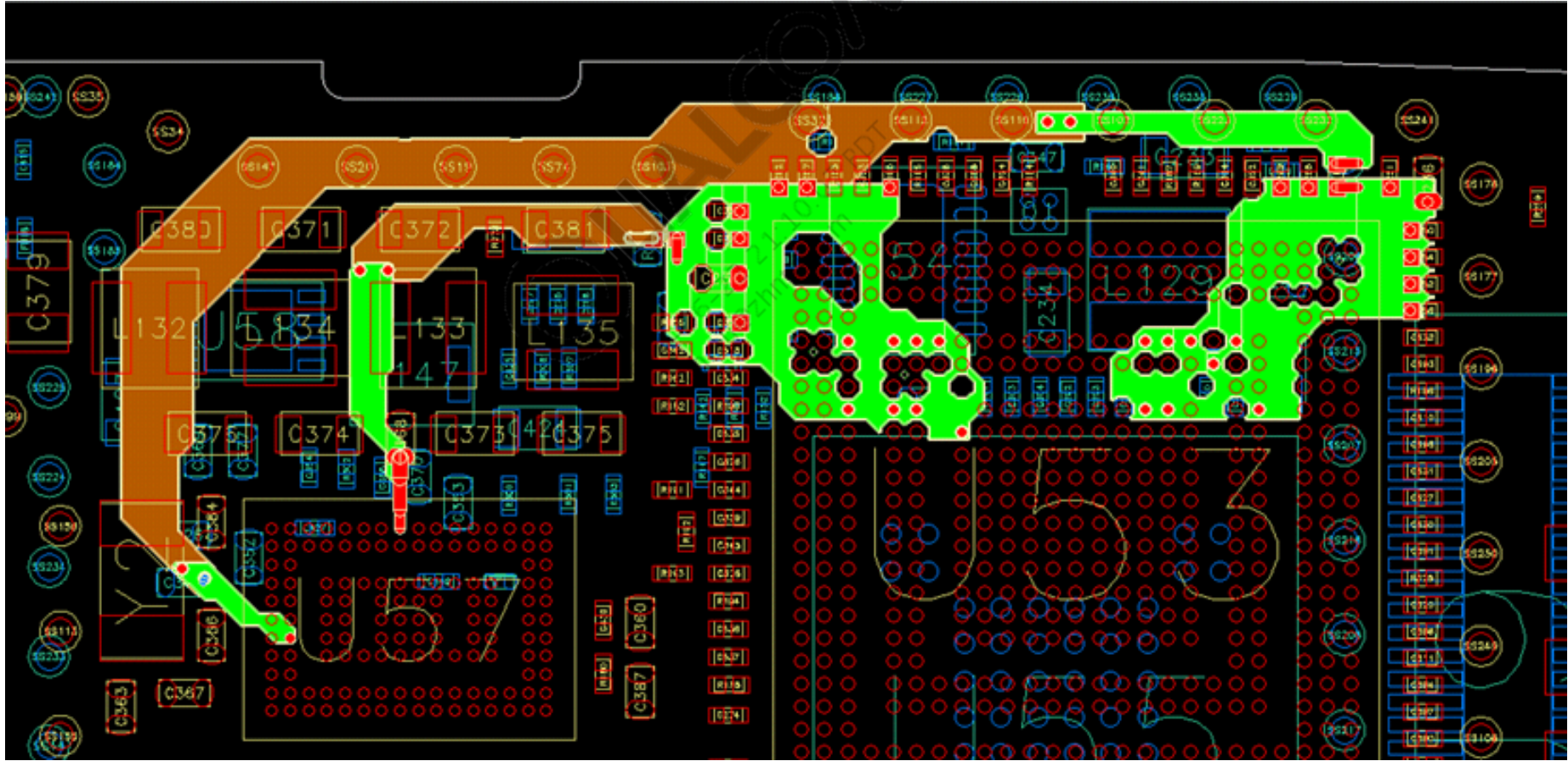
Thermal Design Approach (cont.)

8. Additional considerations:

- Use wide traces, vs. standard width, where possible.
- Use plated mounting holes where possible.
- Use thermal interface material.
 - Helps reduce component case temperature
 - Can also potentially increase the product case touch temperature
 - Be mindful of this trade-off.
- There may be ways to adjust the size and location of thermal hot spots by adding material of various thermal conductivities. This will help to evenly spread thermal dissipation across the entire surface.
- For USB dongle designs, consider reducing the thermal resistance from the PWB through the USB connector to the laptop.
- VCTCXO should be placed in a good spot thermally.
 - Check GSM performance/noise/signal integrity
 - TXCO track LO adjust is also a very sensitive line that needs to be routed carefully

Qualcomm FFA example

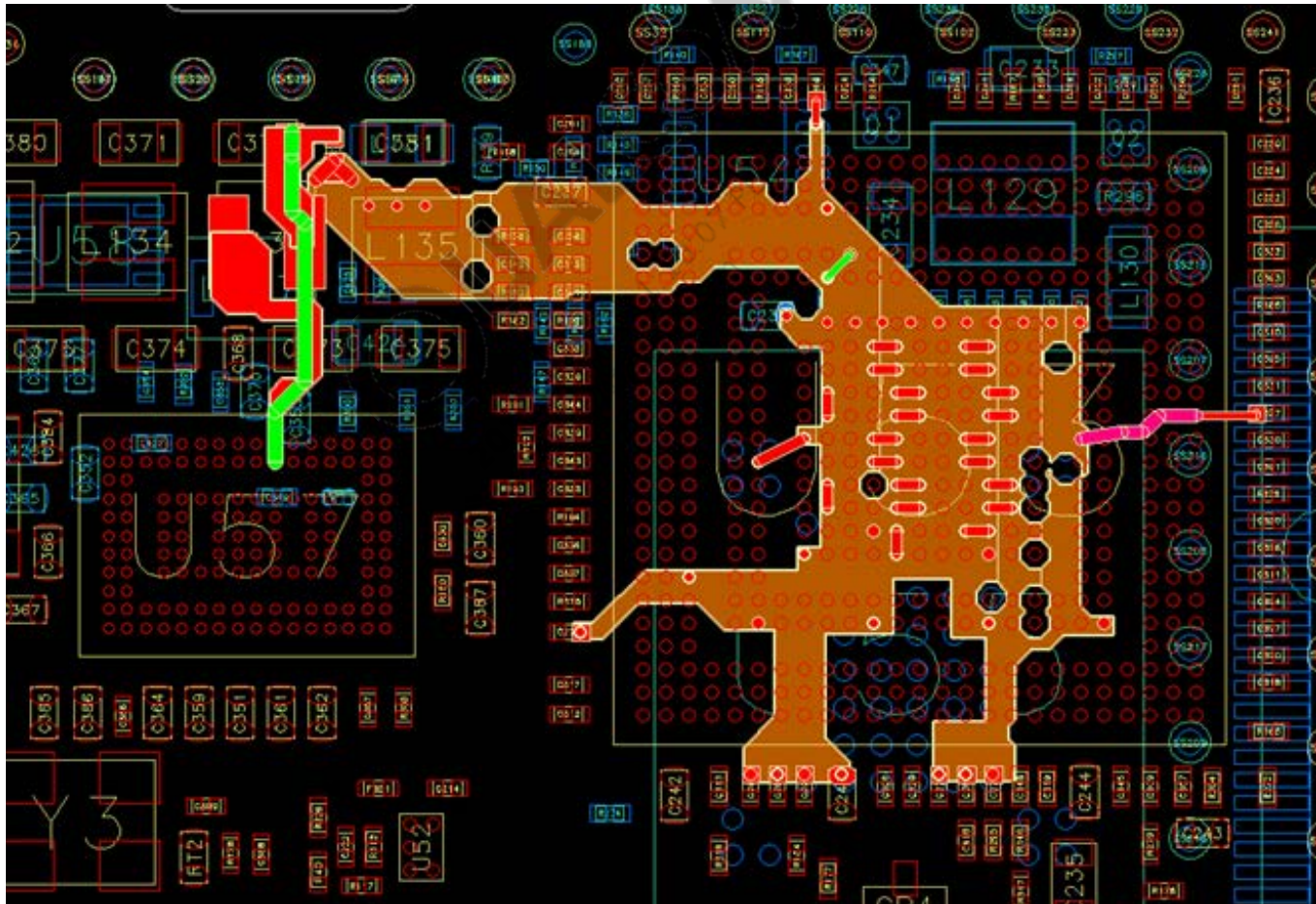
Q6_FW and Q6_SW power



Qualcomm FFA example

Routing VREG_MSMC_1: red layer 1, brown layer 5

Keep it as a plane (red straps are thick traces to MSM pins)



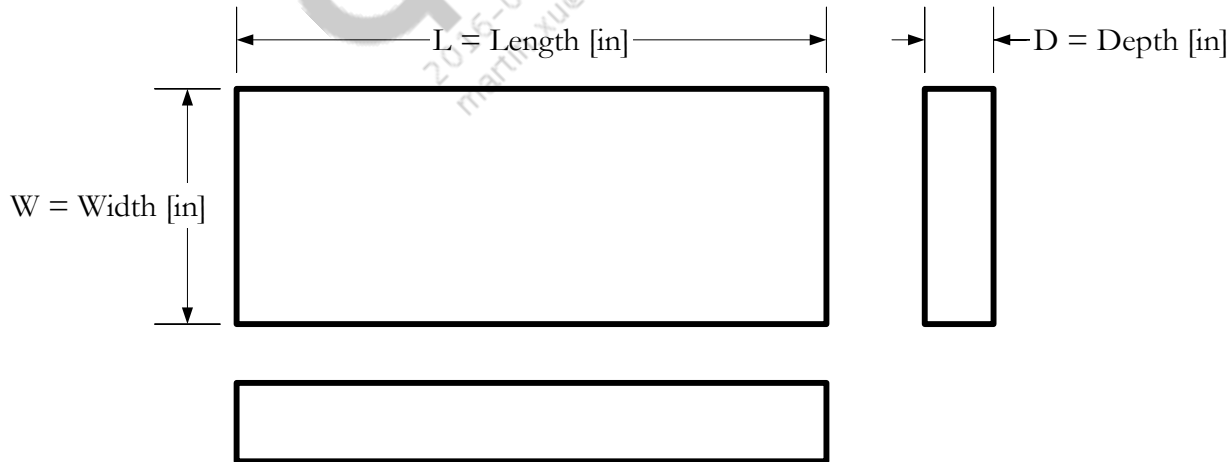
Simple Heat Dissipation (Temperature Rise) Modeling

- Modeling for temperature rising on UE surface:

- Key parameters
 - Total power dissipation
 - Surface area

- Calculate the surface area.

- $A_{surface} = 2(L \times W) + 2(L \times D) + 2(W \times D)$



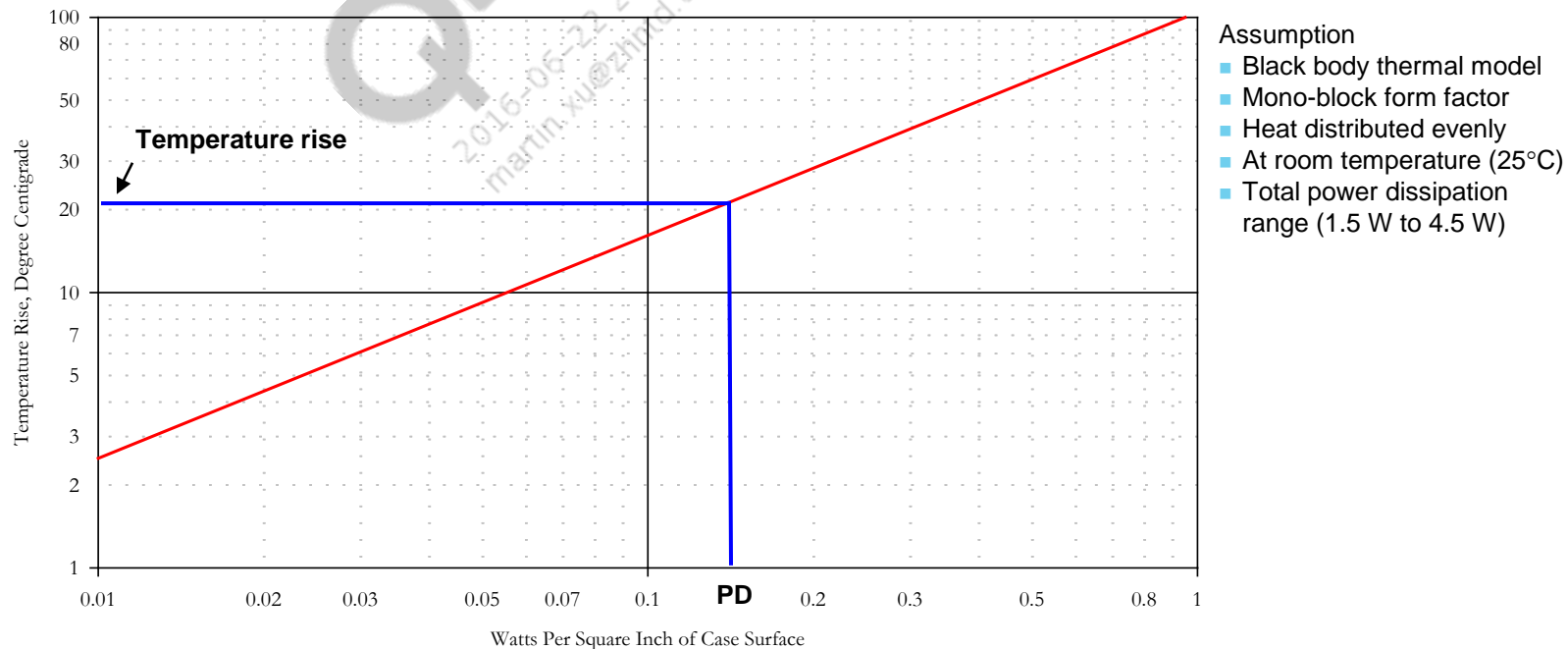
Simple Heat Dissipation (Temperature Rise) Modeling (cont.)

2. Calculate the surface power density.

— $PD_{surface} = P_{average} / A_{surface}$

3. Determine the surface temperature from the T_rise model.

— The average case temperature rise as a function of power density



Thermal Simulation (FloTherm – Fluid Dynamics Software)

- FloTherm:

- 3D computational fluid dynamics software provided by Flometrics
- Predicts airflow and heat transfer in and around electronic equipment
- Includes the coupled effects of conduction, convection, and radiation

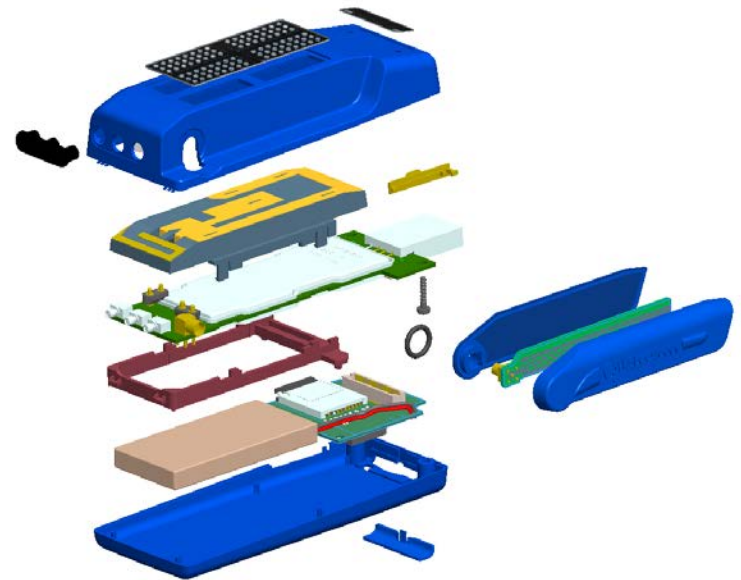
Note: Multiple solution iterations can be run to address design changes and optimization.

- Input:

- Geometry: Size and shape housing parts, PWB with layer count and copper content (in %)
- Materials: Density, specific heat, surface type, and thermal conductivity
- Power: Apply power <watts> to specific parts
- Radiation: Surface exchange accuracy parameter
- Ambient conditions
- Gravity vector
- Grid: Subdivide (finite) volume
- Set for steady state or transient solution

- Output (at each grid point):

- Pressure
- Velocity in vector form
- Temperature in scalar plots



Thermal Simulation (Steady State) Analysis

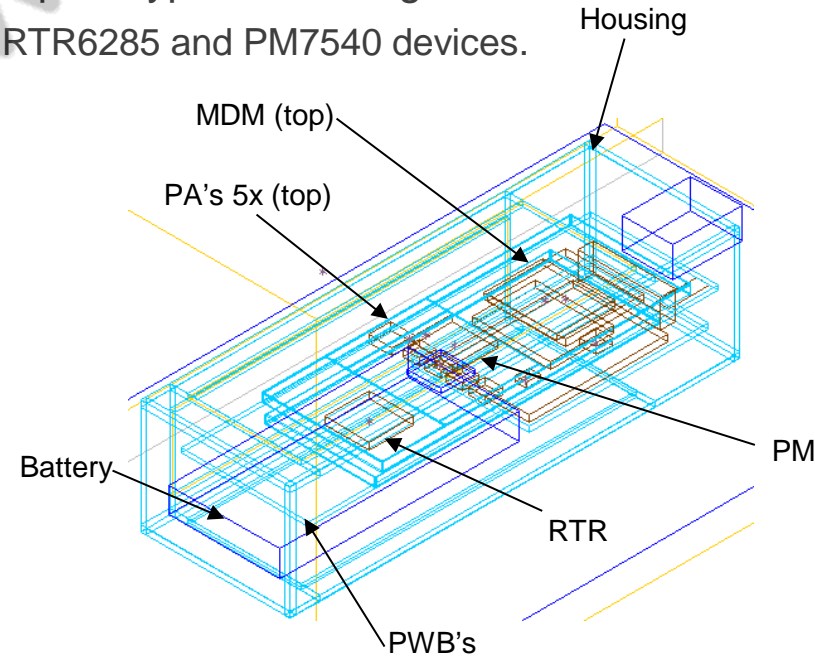
- FloTherm steady state analysis for MDM8200-based prototype USB dongle:
 - The prototype is based on the MDM8200 IC with the RTR6285 and PM7540 devices.

- Model physical:

- Housing: $81 \times 27 \times 20$ mm, 1.0 mm, polycarbonate
- Top vent: 38×14 mm, 20% open
- Shields: $20 \times 55 \times 1.6$ mm and $20 \times 57 \times 1.4$ mm, .17 thick polycarbonate
- Battery size: $43 \times 21 \times 4.7$ mm
- PWB: $73 \times 23 \times .80$, PWB material FR4, 8 layer, 1 and 8 1.4 mil thick cu
- 80% covered, 2 through 7 .7 mil thick cu 50%, 13% by volume, no vias in model
- PWB with sim and SD card, no antenna

- Boundary conditions:

- 35°C ambient
- Unit horizontal with air buoyancy path restriction; no conduction to laptop
- Component power = 2.75 total W (PA 1.07, LTC 0.18, MDM 0.65, PM 0.55, RTR 0.25, battery 0.05, NAND, and VCTCXO zero)



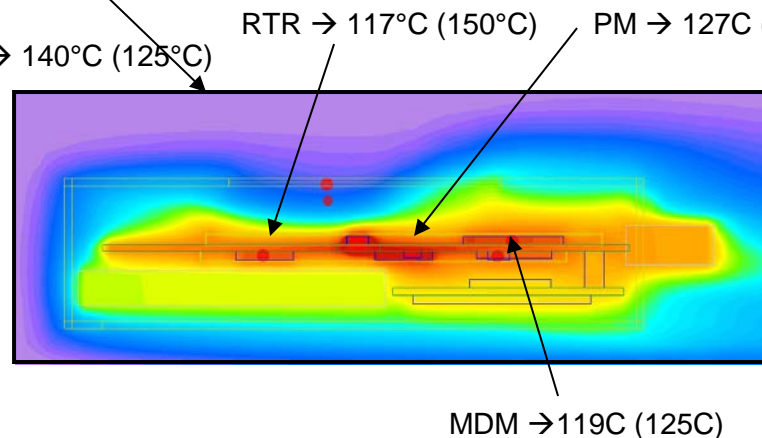
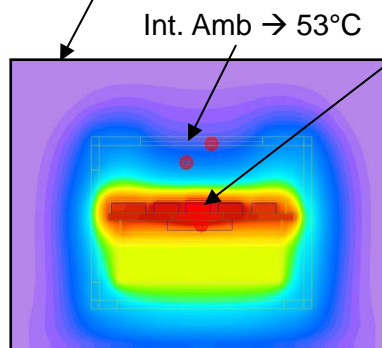
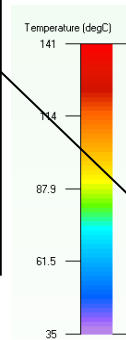
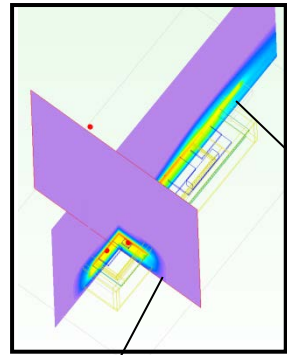
Flotherm wire frame model of Qualcomm prototype

Thermal Simulation (Steady State) Results

FloTherm results for MDM8200-based prototype USB dongle:

■ Conclusion:

- Component junction and maximum junction temperature (shown)
- PA power up to 1.07 W, temperature at 140°C, recommended 85°C, maximum 125°C
- 16 vias around PA (PWB 54 w/mk in-plane conductivity, 0.34 Z axis) increased z axis condition to 0.60, temperature reduced from 150°C to 140°C
- Estimated that PA would need to dissipate 0.91 W to reduce the temperature from 140 to 125°C, and 0.71 W would drop the temperature to 100°C



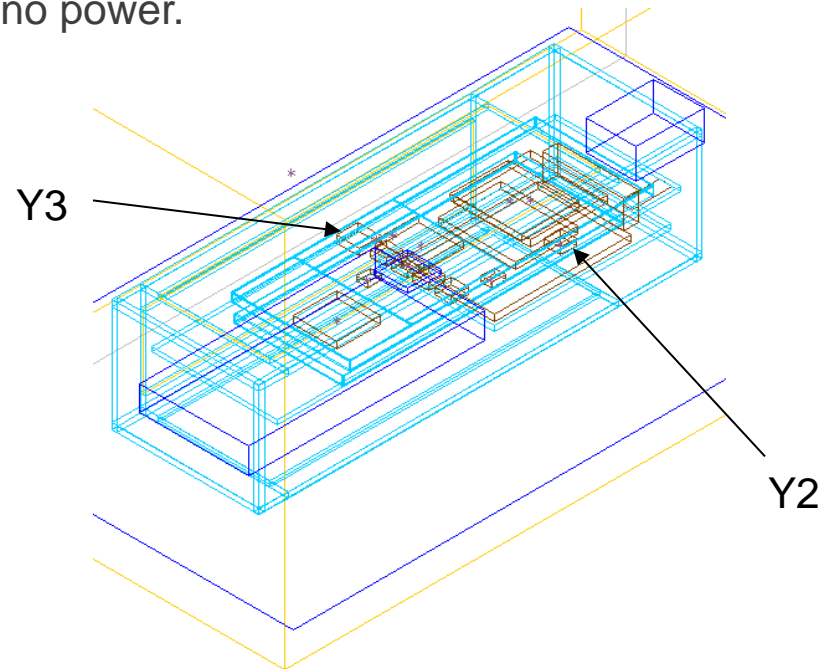
■ Other:

- Top vents drop ambient temperature by 20°C and components by 5°C.
- Side or bottom vents created no change in temperature.
- Metal shields drop PA temperature by 4°C.
- PA thermally conducted to metal shield has no noticeable effect.
- PA temperature will vary based on package size and type.

Thermal Simulation (Transient) Analysis

- FloTherm transient simulation for MDM8200-based prototype USB dongle:
 - Determines thermal time constant and temperature rate of change information for components and housing
- Background:
 - The steady state (ss) component temperatures for PA is 140°C, and VCTCXO is 122°C.
 - This analysis added two components with no power.
 - Y2 – SLEEP_CLK
 - Y3 – VCTCXO

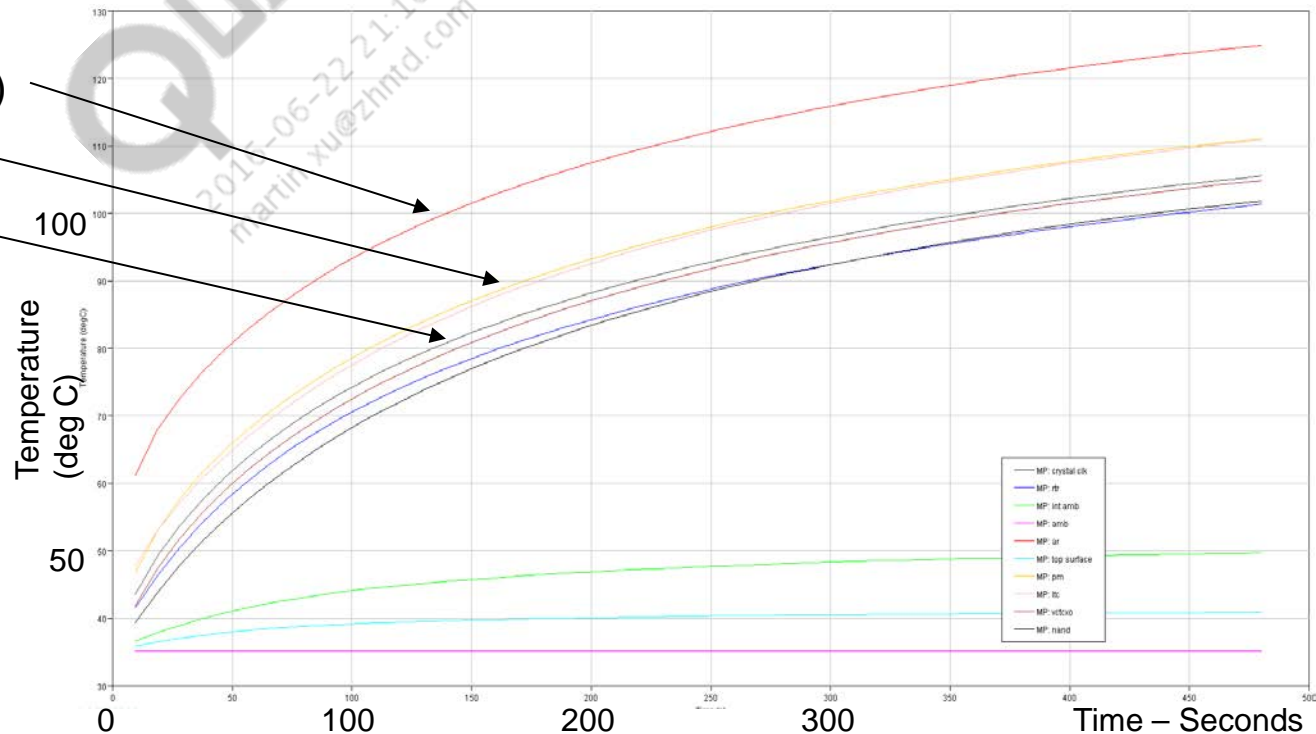
Note: Both are located at bottom of the PCB.



Thermal Simulation (Transient) Results

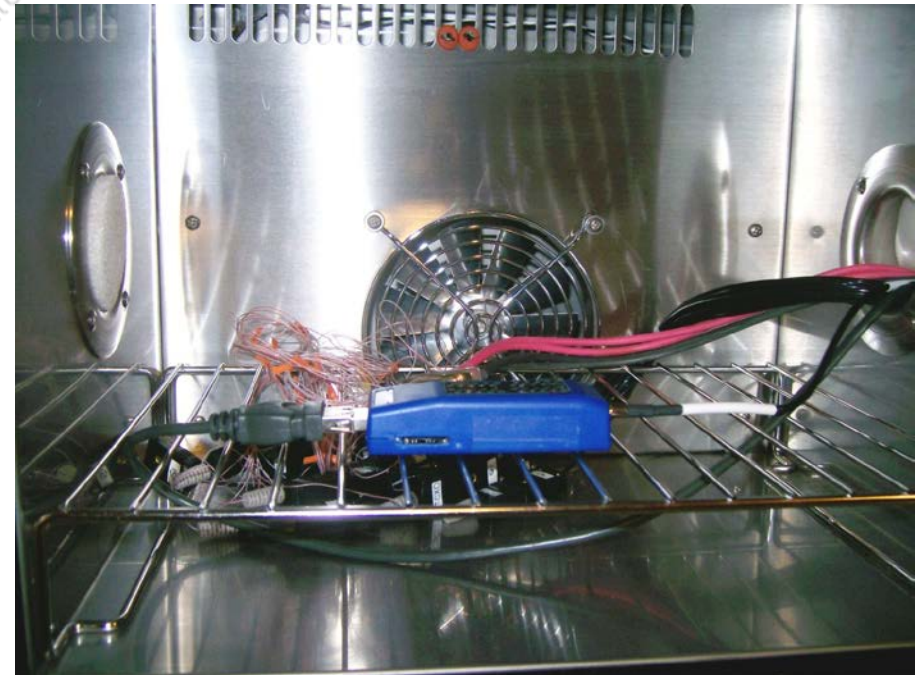
- FloTherm transient analysis for MDM8200-based prototype USB dongle:
- Results: Flotherm result plot is shown below, one time constant (tc) defined as 63% of steady state, approximately 5 tc's to ss.
 - PA: $35 + .63 * (140 - 35) = 101^{\circ}\text{C}$, tc = 137 seconds; rate of change is $66^{\circ}\text{C}/137 \text{ seconds} = 28.9^{\circ}\text{C}/\text{minute}$.
 - VCTCXO: $35 + .63 * (122 - 35) = 89.8^{\circ}\text{C}$, tc = 225 seconds; rate of change is $54.8^{\circ}\text{C}/225 \text{ seconds} = 14.7^{\circ}\text{C}/\text{minute}$.
 - Crystal: $35 + .63 * (110 - 35) = 82.3^{\circ}\text{C}$, tc = 175 seconds; rate of change is $47.3^{\circ}\text{C}/175 \text{ seconds} = 16.2^{\circ}\text{C}/\text{minute}$.
- Conclusion:

- The analysis has a maximum rate of change of the VCTCXO component to be about 14.7°C/minute.
- The VCTCXO goal is to keep change below 1 to 2°C/second, or 60 to 120°C/minute.



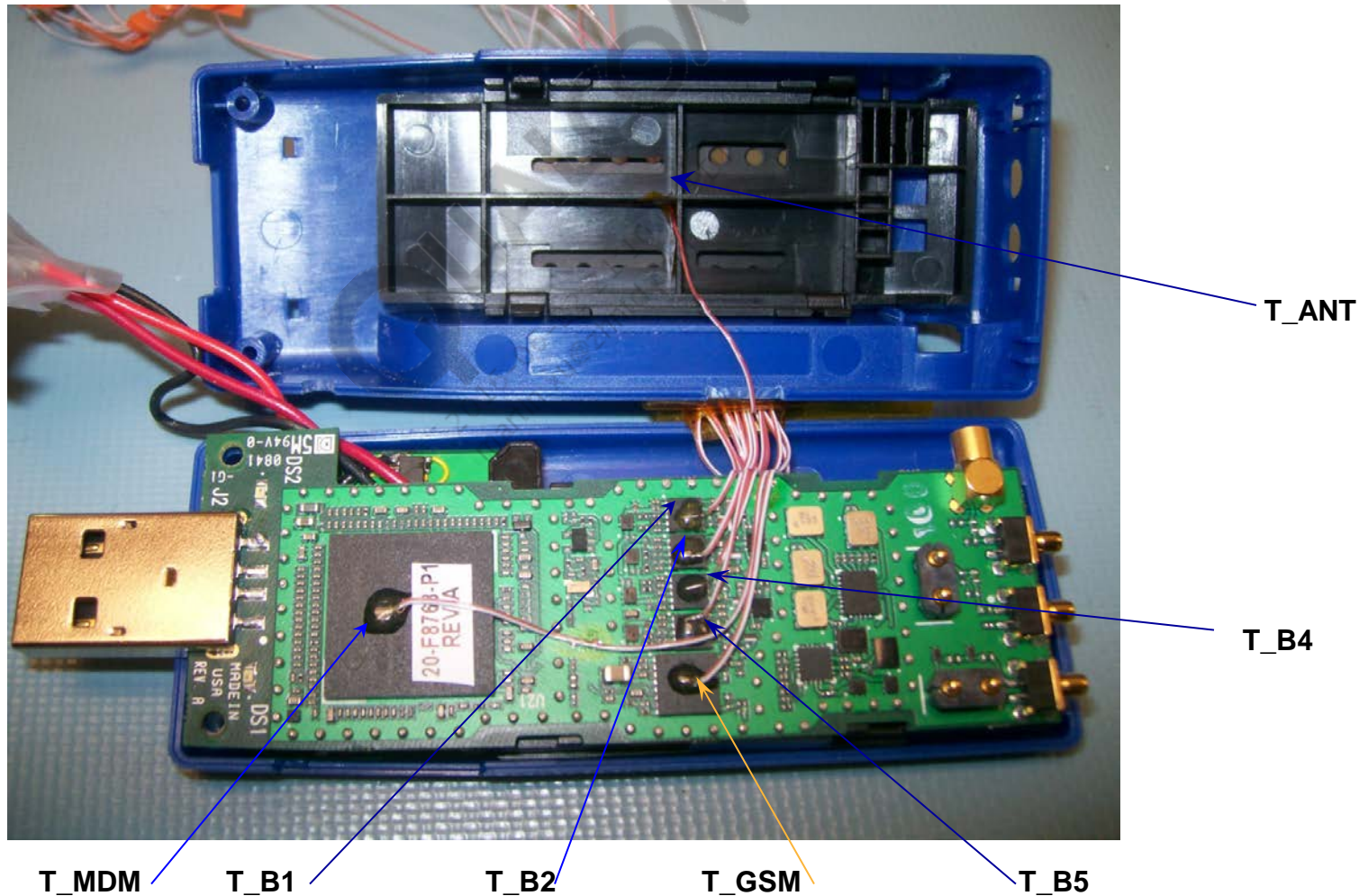
Thermal Testing

- Purpose and results:
 - Validate design approach
 - Confirm simulations
- Testing details:
 - A thermal camera or thermocouples can be used to measure temperatures.
 - The unit under test (UUT) is placed in the oven chamber and protected from the fan air swirl.
 - The design is tested over temperature.
 - The thermocouple wire has two dissimilar conductors joined together at their ends; the thermoelectric voltage developed between the two junctions is proportional to the temperature difference between the junctions.



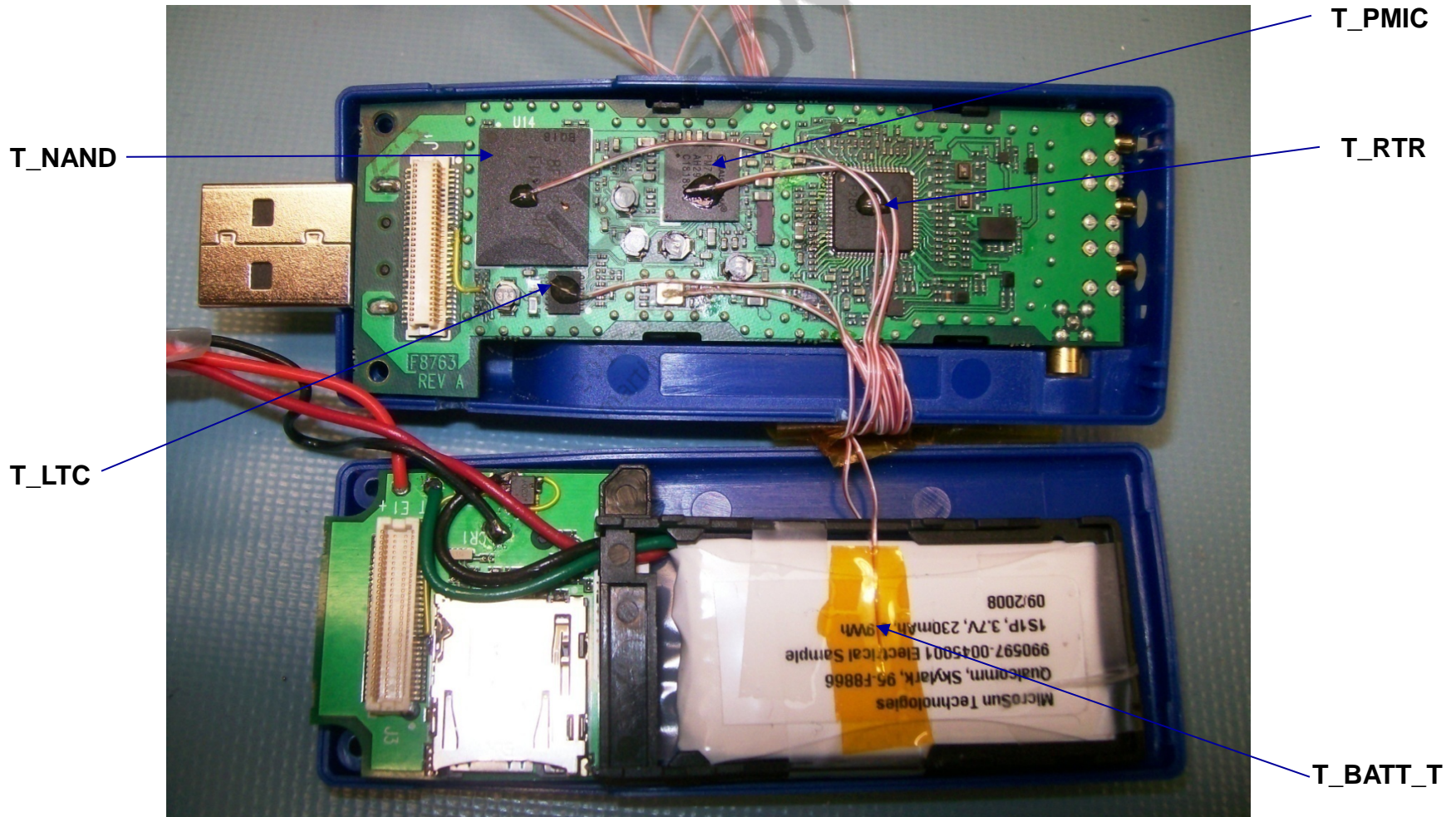
Thermal Testing (cont.)

- Thermocouple connections to components:



Thermal Testing (cont.)

- Thermocouple connections to components:

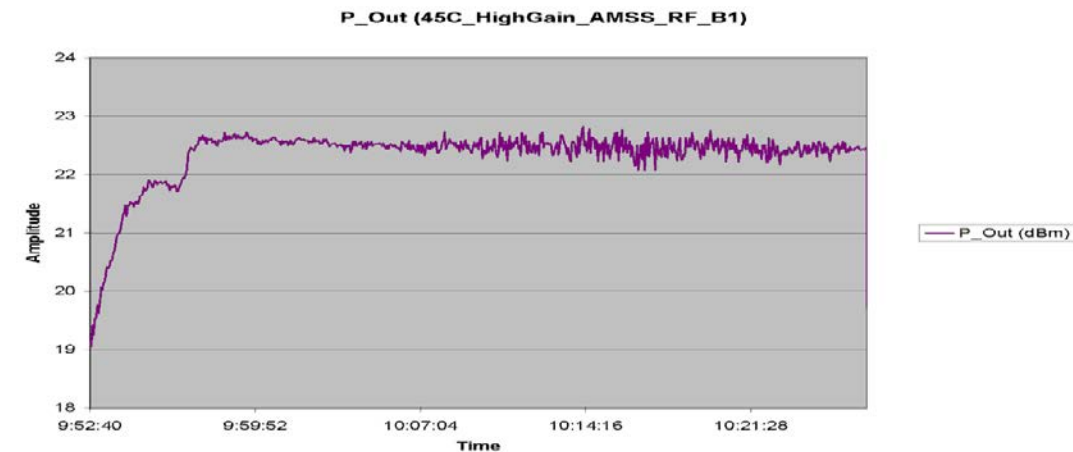
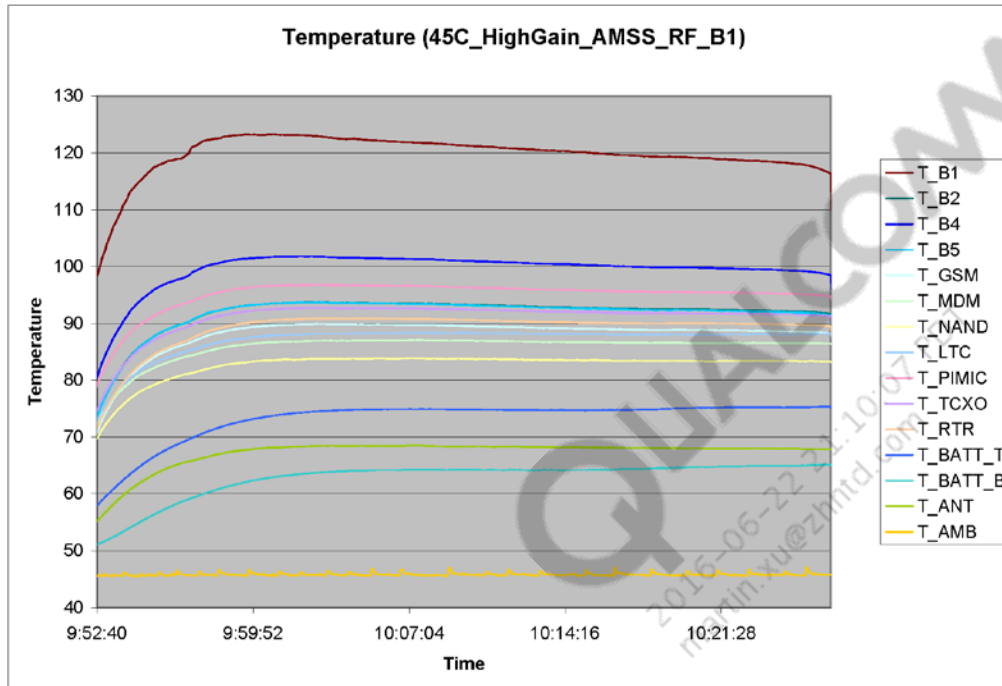


Thermal Testing

- Component part maximum temperature ratings:

Component	Recommended operating temperature (°C)	Absolute maximum temperature (°C)
WCDMA IMT PA (T_B1)	85 (GND pad)	110 (GND pad) 125 (storage)
WCDMA PCS PA (T_B2)	85 (GND pad)	110 (GND pad) 125 (storage)
WCDMA AWS PA (T_B4)	90 (case)	150 (storage)
WCDMA CELL PA (T_B5)	85 (GND pad)	110 (GND pad) 125 (storage)
GSM PA (T_GSM)	85 (case)	150 (storage)
MDM8200 (T_MDM)	100 (case maximum)	150 (storage) 125 (junction)
NAND Flash (T_NAND)	85	150 (storage)
LTC4088 USB/batter power manager (T_LTC)	85	125 (storage) 125 (junction)
PM7540 (T_PMIC)	85 (case maximum)	125 (storage) 150 (junction)
VCTCXO (T_TCXO)	85	85 (storage)
RTR6285 (T_RTR)	85 (case maximum)	150 (storage)
T_BATT_T	45 (charging) 60 (discharging)	

Thermal Testing Results

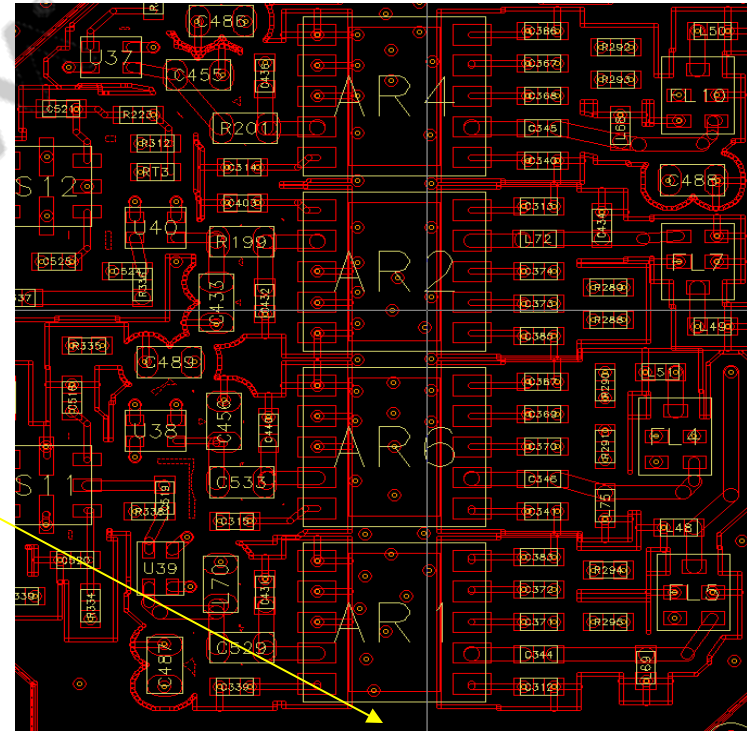
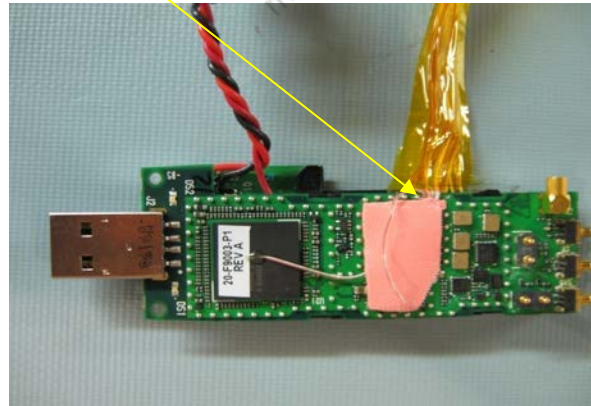


Maximum temperature (°C)

T_B1	123.306
T_B2	93.73
T_B4	101.805
T_B5	93.711
T_GSM	89.9
T_MDM	87.067
T_NAND	83.917
T_LTC	88.37
T_PMIC	96.798
T_TCXO	92.765
T_RTR	90.883
T_BATT_T	75.339
T_BATT_B	65.16
T_ANT	68.545
T_AMB	47.106

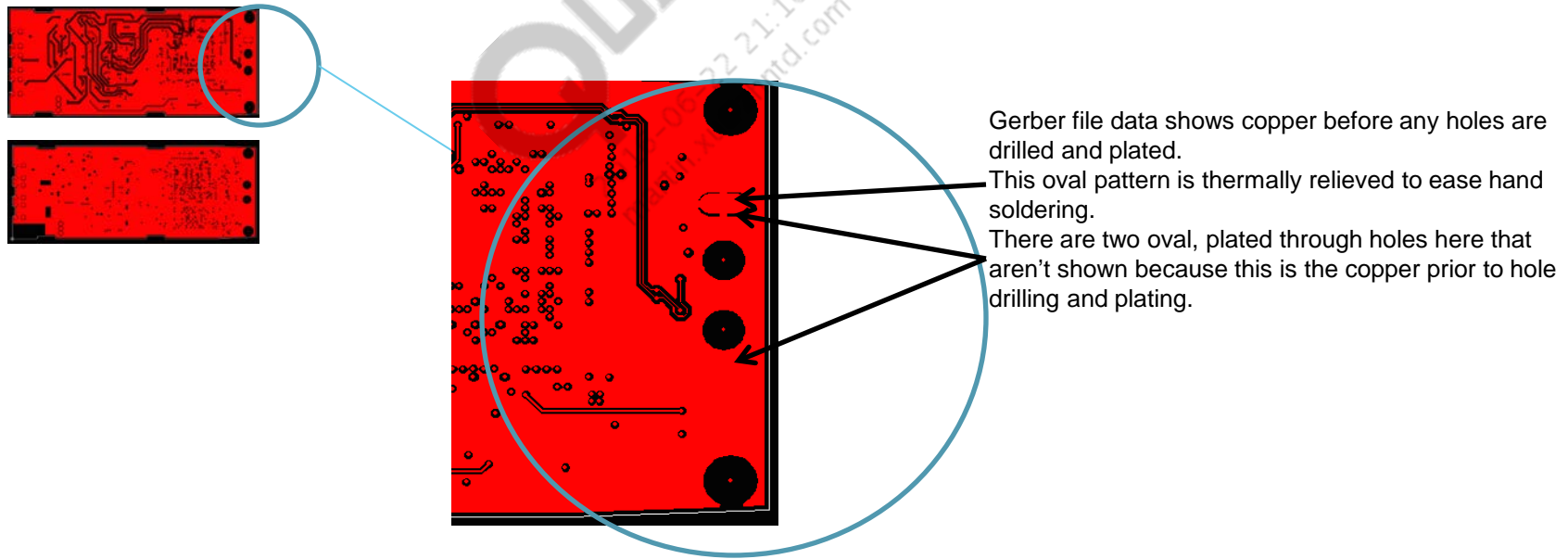
Thermal Testing Conclusion

- Prototype dongle goal and opportunity to lower PA temperature:
 - PWB
 - Added more vias to PWB in area of PAs
 - Reduce temperature as much as 10°C
 - Added gap pad material to the assembly
 - From PAs to shield and on top of shield to spread heat



Copper layer thermal analysis

- Experimental data concluded that copper flooding instead of thermal relief on a single layer of a multiple layer board helps to lower component temperatures on average up to 1°C, without affecting hand solder joint solder time or quality.



Miscellaneous thermal experiments on Qualcomm FFA

- Dongle form factor mitigations to component temperatures:
 - Reducing power consumption on a dongle type product reduces temperatures by 11 to 14°C per watt.
 - Testing a dongle product when connected to a laptop reduces temperatures 3 to 4°C vs. suspended in air with no laptop.
 - Testing a dongle product without baffles to slow chamber air cooling effects reduces measured temperatures by 5 to 10°C.
 - Adding small vents and openings to dongle form factor products with internal shielding reduces temperatures by < 1°C.
 - Adding thermal interface material + graphite to dongle product reduced absolute temperature by 9°C.

Factors That Enhance Thermal for PCB

- For a given circuit board thickness and component design, the temperature of a component on a circuit board tends to be inversely proportional to the amount of copper in the circuit board.
- The temperature of a component on a circuit board can also be related to the thermal conductivity of the circuit board due to the topology of the circuitry.
- The effective conductivity (i.e., ability to dissipate heat) of a circuit board of a given thickness depends on:
 - The finished copper layer thicknesses
 - The number of layers
 - The finished shape of the layers (traces and space)
 - The amount of vias
 - The finished shape of the vias (height, diameter, thickness)
 - The material of the vias

PCB Topology and Fabrication Technology Impact on Thermal

- The topology of the circuitry depends on:
 - The number of vias
 - The relative location of the vias
 - The number of traces
 - The relative location of the traces
- There are different circuit board fabrication methods that are available and they may have different amounts of copper due to the list above.
- There are different circuit board topologies available.
- Consider the effects of circuit board fabrication, design, materials, and topology when designing for thermal performance.

PCB Components Placement Thermal Design

- Avoid double-sided component layout – this will incur
 - Increased heat density
 - Superposition and/dual heating
 - Heat saturation
- Do not reduce spacing between high power components during placement
 - Qualcomm suggests 5 mm minimum spacing (edge-to-edge) – more is better particularly for MSM and PMIC components
 - When compartmentalizing components – do not aggregate high power dissipation component together
- Beef up power and ground plans with copper
- Heat spreading material is a requirement with 100% contact mechanism between spreaders and components

Thermal Protection Algorithm

- As mentioned in the introduction, Qualcomm has developed a thermal protection algorithm that will regulate various RF and USB controls.
- The use of the thermal protection algorithm, with proper design of the USB dongle form factor, should minimize thermal impact.
- See the following documents for more information about the thermal protection algorithm.
 - *Thermal Protection Algorithm Overview* (80-VT344-1)
 - *MDM8200 Thermal Protection Algorithm Application Note* (80-VJ372-14)
 - *MDM9600/MDM9200/MDM8220 Thermal Issues And Protection Software* (80-VP146-28)



Appendix: Heat Transfer Fundamentals

Heat Transfer Fundamentals

- Steady state thermal resistance equation:

- Heat flowing away equals heat generated, heat dissipation is a constant.



$$T = Q R,$$

T is temperature, <degrees Celsius>

Q is heat, <watts>, current flows and heat is generated

R is resistance, <C/W>

- Resistance and three modes of heat transfer:

1. **Conduction** – through solids

$$R = L/K * A, \text{ L = length, K = thermal conductivity, A = area}$$

2. **Convection**

- a. **Forced** – air driven cooling, i.e., fan on components

$$R = 1/h * A$$

Heat Transfer Fundamentals (cont.)

b. Natural – free air buoyancy velocity driven by density change

$R = 1/h * A$, h = heat transfer coefficient, A = area

i. Heat transfer coefficient from a vertical surface

$$h = 0.29 * (\Delta T/L_c)^{.25}, L_c \text{ characteristic length, } = 2 * L * W / (L + W)$$

ii. Heat transfer coefficient from a horizontal surface facing upwards

$$h = 0.27 * (\Delta T/L_c)^{.25}$$

iii. Heat transfer coefficient from a horizontal surface facing downwards

$$h = .13 * (\Delta T/L_c)^{.25}$$

Note: A horizontal surface facing downwards, compared to upwards, has approximately double the heat transfer resistance and will produce double the temperature rise to ambient.

Heat Transfer Fundamentals (cont.)

3. **Radiation** – heat transfer by electromagnetic waves, from surface to surface

$$R = 1 / (\sigma * f * e * A)^{.25}$$

σ = stefan-boltzmann constant

f = view factor – fraction of radiation leaving one surface and intercepted by another

A = area

e = emissivity – radiated from surface relative to 'black body'

b. **Natural** – free air buoyancy velocity driven by density change

$$R = 1/h * A, h = \text{heat transfer coefficient}, A = \text{area}$$

i. Heat transfer coefficient from a vertical surface

$$h = 0.29 * (\Delta T / L_c)^{.25}, L_c \text{ characteristic length, } = 2 * L * W / (L + W)$$

ii. Heat transfer coefficient from a horizontal surface facing upwards

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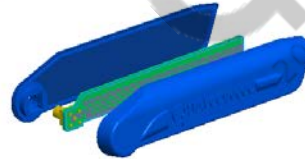
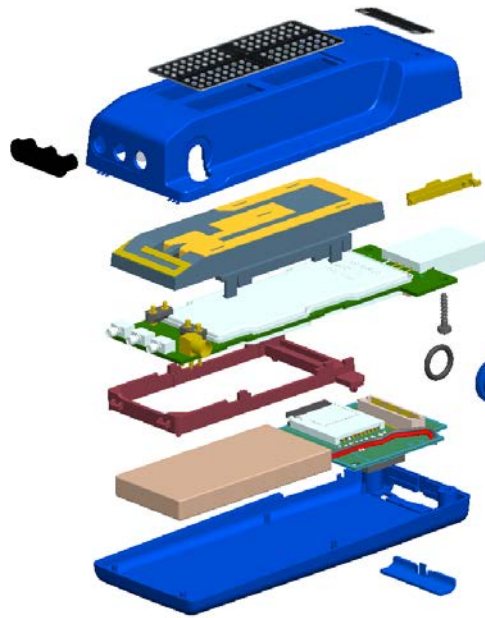
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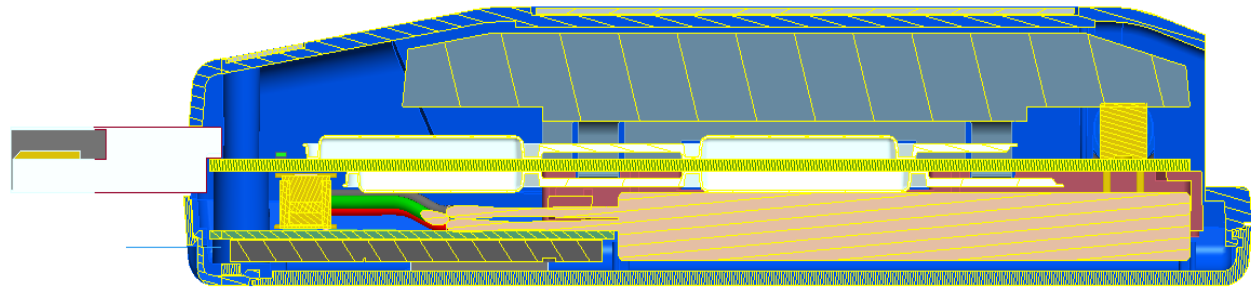
Note: A horizontal surface facing downwards, compared to upwards, has approximately double the heat transfer resistance and will produce double the temperature rise to ambient.

Heat Transfer Fundamentals – USB Dongle Example

- Qualcomm prototype USB dongle thermal resistances example:
 - Prototype based on the MDM8200 IC with the RTR6285 and PM7540 devices
 - Develop thermal resistance network for a generic USB dongle housing assembly
 - Based on heat sources, materials, geometry, and heat transfer modes



$$\Delta T = Q R, R = \text{resistance}$$



Heat Transfer Fundamentals – USB Dongle Example (cont.)

Thermal resistance example

Nodes 2 and 5 are heat sources.

Nodes 1–2: Conduction – component to board

Nodes 2–3: Natural convection and Radiation- component to housing wall

Nodes 3–4: Conduction – through housing wall

Node 4: Ambient: natural convection and radiation – bottom housing to ambient air

Nodes 1–5: Conduction – component to board

Nodes 5–6: Natural Convection and radiation- component to housing wall

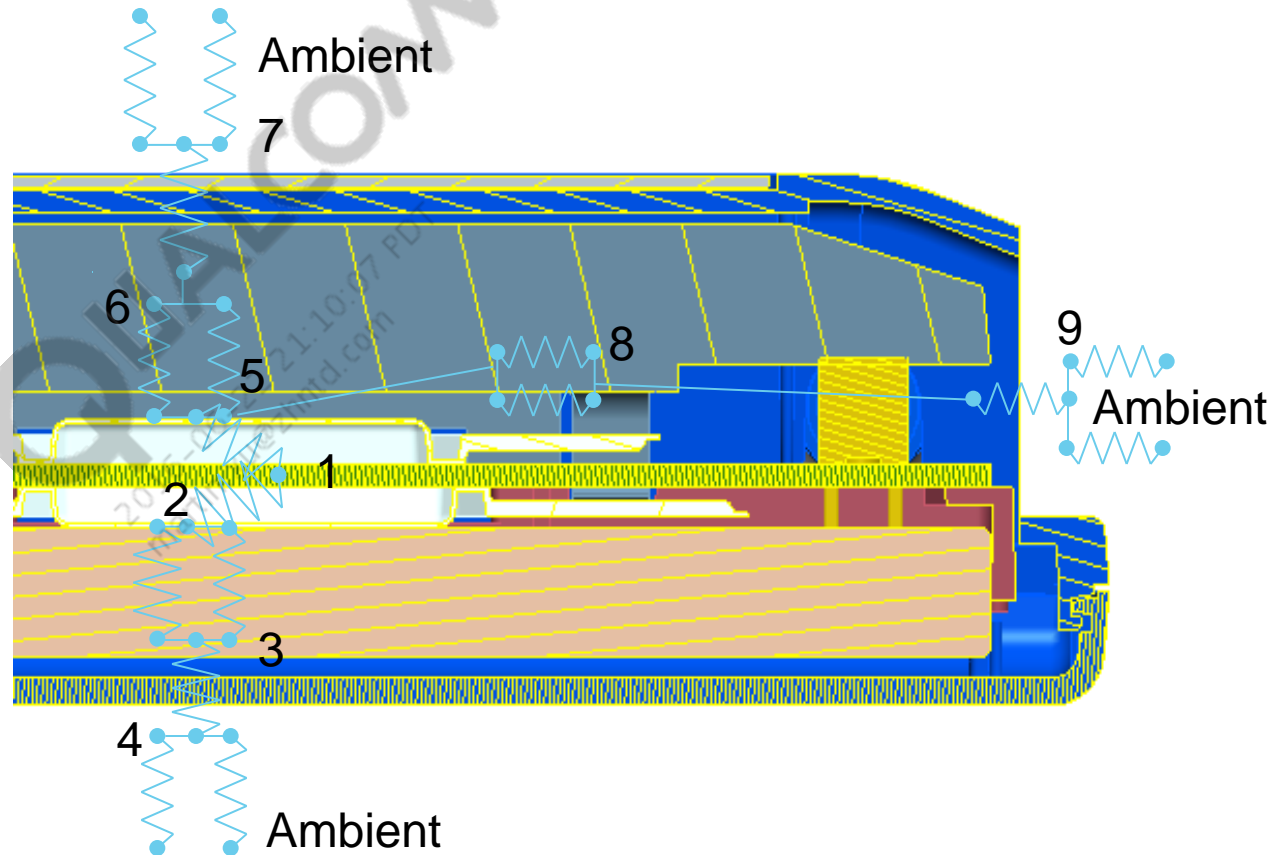
Nodes 6–7: Conduction – Through housing wall

Node 7: Ambient: natural convection and radiation – top housing to ambient air

Nodes 5–8: Natural convection and radiation- component to housing wall

Nodes 8–9: Conduction – through housing wall

Node 9: Ambient: natural convection and radiation – side housing to ambient air



Note: Convection and conduction heat transfer dominates the cooling of the USB dongle.

Questions?

You may also submit questions to:

<https://support.cdmatech.com>

